

21 *and*
a second conductive layer comprising a film of conductive layer, at least partially overlapping the data lines in a plan view.

26. (Twice Amended) A method for fabricating an electro-optical device comprising a substrate, a plurality of scanning lines, a plurality of data lines, a thin-film transistor disposed in correspondence with intersections of the plurality of data lines and the plurality of scanning lines, and a pixel electrode disposed in correspondence with the thin-film transistor, the method comprising the steps of:

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forming a semiconductor layer for producing a source region, a channel region, and a drain region on the substrate;

forming an insulating thin film on the semiconductor layer;

forming the scanning lines and one electrode of a storage capacitor on the insulating thin film;

forming a first interlayer insulating film on the scanning lines and the one electrode;

making a first contact hole leading to the semiconductor layer in the insulating film and the first interlayer insulating film;

forming a light-shielding first conductive layer on the first interlayer insulating film so as to be electrically connected to the semiconductor layer through the first contact hole and forming a second conductive layer comprising a film of conductive layer;

forming a second interlayer insulating film on the first conductive layer and the second conductive layer;

forming the data lines on the second interlayer insulating film above the second conductive layer;

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forming a third interlayer insulating film on the data lines;

making a second contact hole leading to the first conductive layer in the second interlayer insulating film and the third interlayer insulating film; and

forming the pixel electrode so as to be electrically connected to the first conductive layer through the second contact hole,

the second conductive layer being formed so as to at least partially overlap the data lines in a plan view.

28. (Twice Amended) A method for fabricating an electro-optical device comprising a substrate, a plurality of scanning lines, a plurality of data lines, a thin-film transistor disposed in correspondence with intersections of the plurality of data lines and the plurality of scanning lines, and a pixel electrode disposed in correspondence with the thin-film transistor, the method comprising the steps of:

forming a semiconductor layer for producing a source region, a channel region, and a drain region on the substrate;

forming an insulating thin film on the semiconductor layer;

forming the scanning lines and one electrode of a storage capacitor on the insulating thin film;

forming a first interlayer insulating film on the scanning lines and the one electrode of the storage capacitor;

making a first contact hole leading to the semiconductor layer in the first interlayer insulating film;

forming the data lines on the first interlayer insulating film and simultaneously forming an interconnecting conductive layer comprising a film comprising the data lines so as to be electrically connected to the semiconductor layer through the first contact hole;

forming a second interlayer insulating film on the data lines and the interconnecting conductive layer;

making a second contact hole leading to the interconnecting conductive layer
in the second interlayer insulating film;

forming a light-shielding first conductive film on the second interlayer
insulating film so as to be electrically connected to the interconnecting conductive layer
through the second contact hole, and simultaneously forming a second conductive layer
comprising a film of conductive layer disposed below the data lines so as to overlap the data
lines in a plan view;

forming a third interlayer insulating film on the first conductive layer and the
second conductive layer;

making a third contact hole leading to the first conductive layer in the third
interlayer insulating film; and

forming the pixel electrode so as to be electrically connected to the first conductive
layer through the third contact hole.

Please add new claim 31 as follows:

--31. The electro-optical device according to claim 1, the first conductive layer and
the second conductive layer being formed with a same film.--

REMARKS

Claims 1-31 are pending. By this Amendment, claims 1, 26 and 28 are amended;
claim 31 is added; and formal drawings are provided by the Letter to Official Draftsperson as
attached herewith. Reconsideration based on the above amendments and following remarks
is respectfully requested.

The attached Appendix includes a marked-up copy of each rewritten claim (37 C.F.R.
§1.121(c)(1)(ii)).